

LDO Regulator, 100 mA, 18 V, 1 μ A I_Q , with PG NCV8711

The NCV8711 device is based on unique combination of features – very low quiescent current, fast transient response and high input and output voltage ranges. The NCV8711 is CMOS LDO regulator designed for up to 18 V input voltage and 100 mA output current. Quiescent current of only 1 μ A makes this device ideal solution for battery-powered, always-on systems. Several fixed output voltage versions are available as well as the adjustable version.

The device (version B) implements power good circuit (PG) which indicates that output voltage is in regulation. This signal could be used for power sequencing or as a microcontroller reset.

Internal short circuit and over temperature protections saves the device against overload conditions.

Features

- Operating Input Voltage Range: 2.7 V to 18 V
- Output Voltage: 1.2 V to 17 V
- Capable of Sourcing 140 mA Peak Output Current
- Very Low Quiescent Current: 1 μ A typ.
- Low Dropout: 215 mV typ. at 100 mA
- Output Voltage Accuracy $\pm 1\%$
- Power Good Output (Version B)
- Stable with Small 1 μ F Ceramic Capacitors
- Built-in Soft Start Circuit to Suppress Inrush Current
- Over-Current and Thermal Shutdown Protections
- Available in Small TSOP-5 and WDFNW6 (2x2) Packages
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

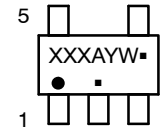
Typical Applications

- Body Control Modules
- LED Lighting
- On Board Charger
- General Purpose Automotive

MARKING DIAGRAMS

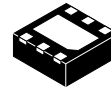


TSOP-5
CASE 483
SN SUFFIX

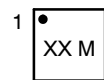


XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

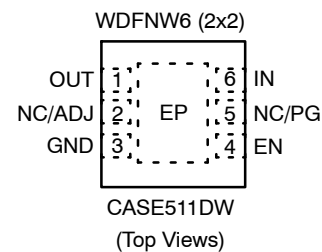
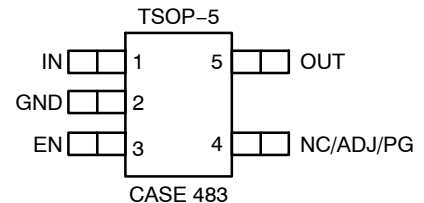


WDFNW6 (2x2)
CASE 511DW
MTW SUFFIX



XX = Specific Device Code
M = Date Code

PIN ASSIGNMENTS



ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

TYPICAL APPLICATION SCHEMATICS

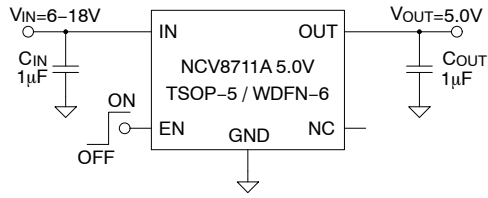


Figure 1. Fixed Output Voltage Application (No PG)

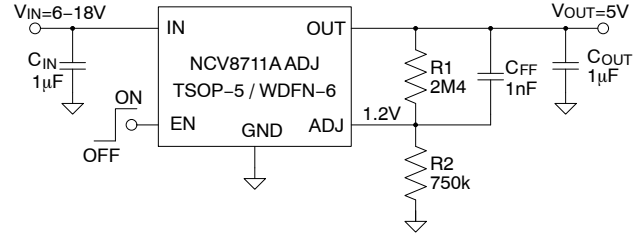


Figure 2. Adjustable Output Voltage Application (No PG)

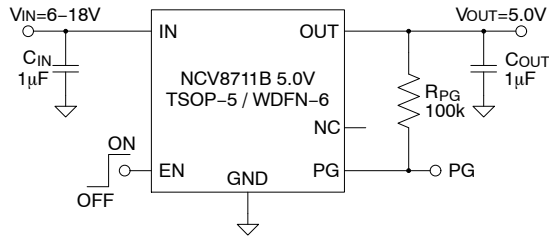


Figure 3. Fixed Output Voltage Application with PG

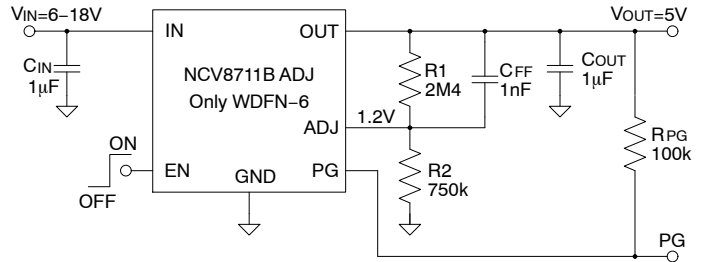
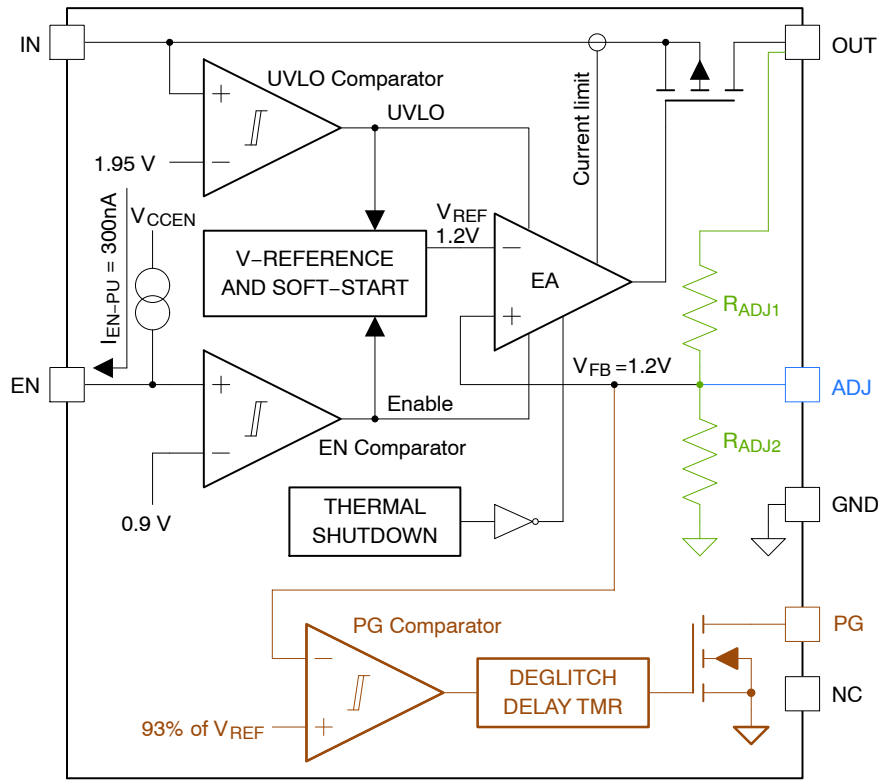


Figure 4. Adjustable Output Voltage Application with PG

$$V_{OUT} = V_{ADJ} \cdot \left(1 + \frac{R_1}{R_2}\right) + I_{ADJ} \cdot R_1$$

SIMPLIFIED BLOCK DIAGRAMS



Note: Blue objects are valid for ADJ version
 Green objects are valid for FIX version
 Brown objects are valid for B version (with PG)

Figure 5. Internal Block Diagram

PIN DESCRIPTION

Pin No. TSOP-5	Pin No. WDFNW6	Pin Name	Description
1	6	IN	Power supply input pin.
2	3	GND	Ground pin.
5	1	OUT	LDO output pin.
3	4	EN	Enable input pin (high – enabled, low – disabled). If this pin is connected to IN pin or if it is left unconnected (pull-up resistor is not required) the device is enabled.
4 (Note 1)	2	ADJ	Adjust input pin. Connect it to the output resistor divider or directly to the OUT pin.
4 (Note 1)	5	PG	Power good output pin. Could be left unconnected or could be connected to GND if not needed. High level for power ok, low level for fail.
4 (Note 1)	2, 5	NC	Not internally connected. This pin can be tied to the ground plane to improve thermal dissipation.
NA	EP	EPAD	Connect the exposed pad to GND.

1. Pin function depends on device version.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
VIN Voltage (Note 2)	V _{IN}	−0.3 to 22	V
VOU Voltage	V _{OUT}	ADJ version & FIX versions V _{OUT-NOM} > 5.0 V: −0.3 to [(V _{IN} + 0.3) or 22; whichever is lower] FIX versions V _{OUT-NOM} ≤ 5.0 V: −0.3 to [(V _{IN} + 0.3) or 6.0; whichever is lower]	V
EN Voltage	V _{EN}	−0.3 to (V _{IN} + 0.3)	V
ADJ Voltage	V _{FB/ADJ}	−0.3 to 5.5	V
PG Voltage	V _{PG}	−0.3 to (V _{IN} + 0.3)	V
Output Current	I _{OUT}	Internally limited	mA
PG Current	I _{PG}	3	mA
Maximum Junction Temperature	T _{J(MAX)}	150	°C
Storage Temperature	T _{STG}	−55 to 150	°C
ESD Capability, Human Body Model (Note 3)	ESD _{HBM}	2000	V
ESD Capability, Charged Device Model (Note 3)	ESD _{CDM}	1000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

3. This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per ANSI/ESDA/JEDEC JS-001, EIA/JESD22-A114 (AEC-Q100-002)

ESD Charged Device Model tested per ANSI/ESDA/JEDEC JS-002, EIA/JESD22-C101 (AEC-Q100-011D)

THERMAL CHARACTERISTICS (Note 4)

Characteristic	Symbol	WDFNW6 2x2	TSOP-5	Unit
Thermal Resistance, Junction-to-Air	R _{thJA}	67	178	°C/W
Thermal Resistance, Junction-to-Case (top)	R _{thJCt}	89	93	°C/W
Thermal Resistance, Junction-to-Case (bottom)	R _{thJCb}	11	N/A	°C/W
Thermal Resistance, Junction-to-Board (top)	R _{thJBt}	44	53	°C/W
Thermal Characterization Parameter, Junction-to-Case (top)	Ψ _{siJCt}	4.6	18	°C/W
Thermal Characterization Parameter, Junction-to-Board [FEM]	Ψ _{siJB}	44	53	°C/W

4. Measured according to JEDEC board specification (board 1S2P, Cu layer thickness 1 oz, Cu area 650 mm², no airflow). Detailed description of the board can be found in JESD51-7.

ELECTRICAL CHARACTERISTICS (V_{IN} = V_{OUT-NOM} + 1 V and V_{IN} ≥ 2.7 V, V_{EN} = 1.2 V, I_{OUT} = 1 mA, C_{IN} = C_{OUT} = 1.0 μF (effective capacitance – Note 5), T_J = −40°C to 125°C, ADJ tied to OUT, unless otherwise specified) (Note 6)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Recommended Input Voltage		V _{IN}	2.7	–	18	V
Output Voltage Accuracy	T _J = −40°C to +85°C	V _{OUT}	−1	–	1	%
	T _J = −40°C to +125°C		−1	–	2	
ADJ Reference Voltage	ADJ version only	V _{ADJ}	–	1.2	–	V
ADJ Input Current	V _{ADJ} = 1.2 V	I _{ADJ}	−0.1	0.01	0.1	μA
Line Regulation	V _{IN} = V _{OUT-NOM} + 1 V to 18 V and V _{IN} ≥ 2.7 V	ΔV _{O(ΔVI)}	–	–	0.2	%V _{OUT}
Load Regulation	I _{OUT} = 0.1 mA to 100 mA	ΔV _{O(ΔIO)}	–	–	0.4	%V _{OUT}
Quiescent Current (version A)	V _{IN} = V _{OUT-NOM} + 1 V to 18 V, I _{OUT} = 0 mA	I _Q	–	1.3	2.5	μA
Quiescent Current (version B)	V _{IN} = V _{OUT-NOM} + 1 V to 18 V, I _{OUT} = 0 mA		–	1.8	3.0	
Ground Current	I _{OUT} = 100 mA	I _{GND}	–	325	450	μA
Shutdown Current (Note 10)	V _{EN} = 0 V, I _{OUT} = 0 mA, V _{IN} = 18 V	I _{SHDN}	–	0.35	1.5	μA
Output Current Limit	V _{OUT} = V _{OUT-NOM} − 100 mV	I _{OLIM}	140	250	450	mA
Short Circuit Current	V _{OUT} = 0 V	I _{OSC}	140	250	450	mA



ELECTRICAL CHARACTERISTICS ($V_{IN} = V_{OUT-NOM} + 1$ V and $V_{IN} \geq 2.7$ V, $V_{EN} = 1.2$ V, $I_{OUT} = 1$ mA, $C_{IN} = C_{OUT} = 1.0$ μ F (effective capacitance – Note 5), $T_J = -40^\circ\text{C}$ to 125°C , ADJ tied to OUT, unless otherwise specified) (Note 6) (continued)

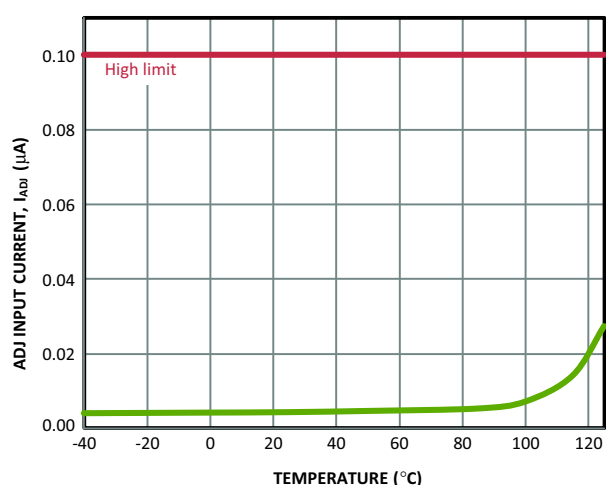
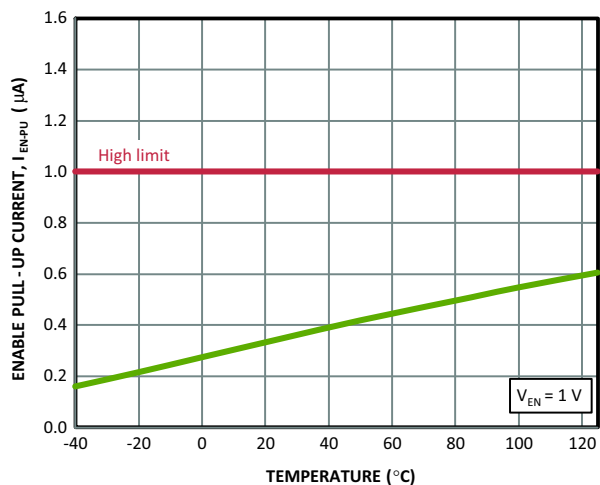
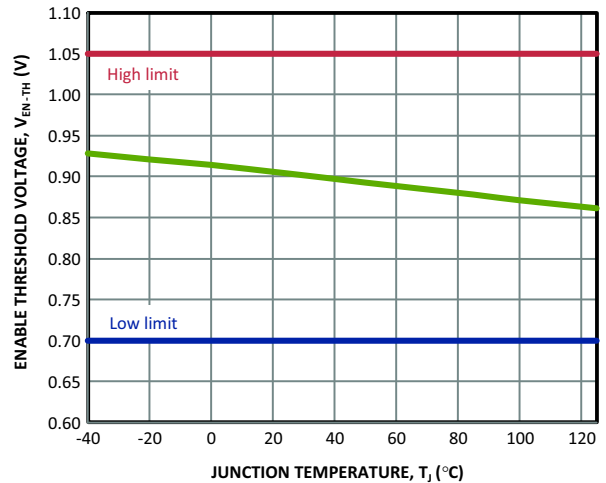
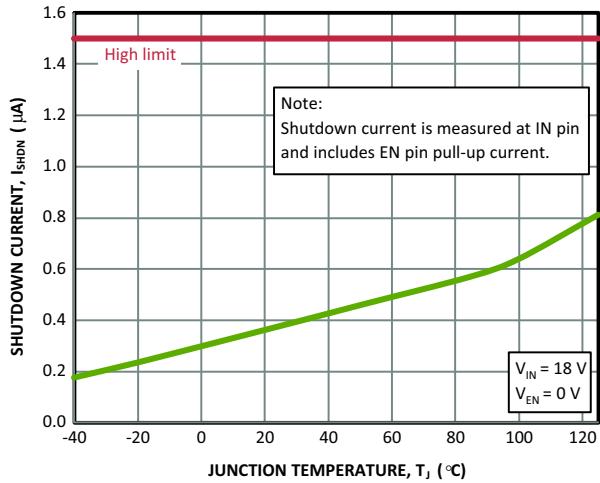
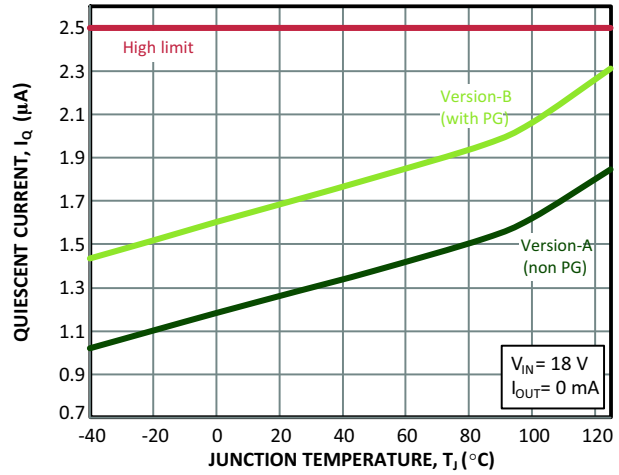
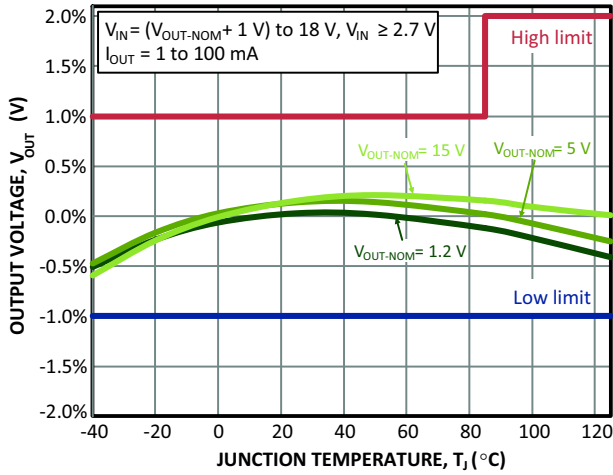
Parameter	Test Conditions		Symbol	Min	Typ	Max	Unit
Dropout Voltage (Note 7)	I _{OUT} = 100 mA		V _{DO}	–	215	355	mV
Power Supply Ripple Rejection	V _{IN} = V _{OUT-NOM} + 2 V I _{OUT} = 10 mA	10 Hz	PSRR	–	80	–	dB
		10 kHz		–	70	–	
		100 kHz		–	42	–	
		1 MHz		–	48	–	
Output Noise	f = 10 Hz to 100 kHz, V _{OUT-NOM} = 5.0 V		V _N	–	240	–	μV _{RMS}
EN Threshold	V _{EN} rising		V _{EN-TH}	0.7	0.9	1.05	V
EN Hysteresis	V _{EN} falling		V _{EN-HY}	0.01	0.1	0.2	V
EN Internal Pull-up Current	V _{EN} = 1 V, V _{IN} = 5.5 V		I _{EN-PU}	0.01	0.3	1	μA
EN Input Leakage Current	V _{EN} = 18 V, V _{IN} = 18 V		I _{EN-LK}	–1	0.05	1	μA
Start-up time (Note 8)	V _{OUT-NOM} ≤ 3.3 V		t _{START}	100	250	500	μs
	V _{OUT-NOM} > 3.3 V			300	600	1000	
Internal UVLO Threshold	Ramp V _{IN} up until output is turned on		V _{IUL-TH}	1.6	1.95	2.6	V
Internal UVLO Hysteresis	Ramp V _{IN} down until output is turned off		V _{IUL-HY}	0.05	0.2	0.3	V
PG Threshold (Note 9)	V _{OUT} falling		V _{PG-TH}	90	93	96	%
PG Hysteresis (Note 9)	V _{OUT} rising		V _{PG-HY}	0.1	2	4	%
PG Deglitch Time (Note 9)			t _{PG-DG}	75	160	270	μs
PG Delay Time (Note 9)			t _{PG-DLY}	120	320	600	μs
PG Output Low Level Voltage (Note 9)	I _{PG} = 1 mA		V _{PG-OL}	–	0.2	0.4	V
PG Output Leakage Current (Note 9)	V _{PG} = 18 V		I _{PG-LK}	–	0.01	1	μA
Thermal Shutdown Temperature	Temperature rising from T _J = +25°C		T _{SD}	–	165	–	°C
Thermal Shutdown Hysteresis	Temperature falling from T _{SD}		T _{SDH}	–	20	–	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Effective capacitance, including the effect of DC bias, tolerance and temperature. See the Application Information section for more information.
- Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at $T_A = 25^\circ\text{C}$. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.
- Dropout measured when the output voltage falls 100 mV below the nominal output voltage. Limits are valid for all voltage versions with nominal output voltage higher than or equal to 2.5 V. For lower output voltage versions, the dropout test is not applied because the input voltage during the test would fall below the minimum input voltage 2.7 V.
- Startup time is the time from EN assertion to point when output voltage is equal to 95% of $V_{OUT-NOM}$.
- Applicable only to version B (device option with power good output). PG threshold and PG hysteresis are expressed in percentage of nominal output voltage.
- Shutdown current includes EN Internal Pull-up Current.

TYPICAL CHARACTERISTICS

$V_{IN} = V_{OUT-NOM} + 1\text{ V}$ AND $V_{IN} \geq 2.7\text{ V}$, $V_{EN} = 1.2\text{ V}$, $I_{OUT} = 1\text{ mA}$, $C_{OUT} = 1.0\text{ MF}$, ADJ TIED TO OUT, $T_J = 25^\circ\text{C}$, UNLESS OTHERWISE SPECIFIED



TYPICAL CHARACTERISTICS

$V_{IN} = V_{OUT-NOM} + 1\text{ V}$ AND $V_{IN} \geq 2.7\text{ V}$, $V_{EN} = 1.2\text{ V}$, $I_{OUT} = 1\text{ mA}$, $C_{OUT} = 1.0\text{ MF}$, ADJ TIED TO OUT, $T_J = 25^\circ\text{C}$, UNLESS OTHERWISE SPECIFIED

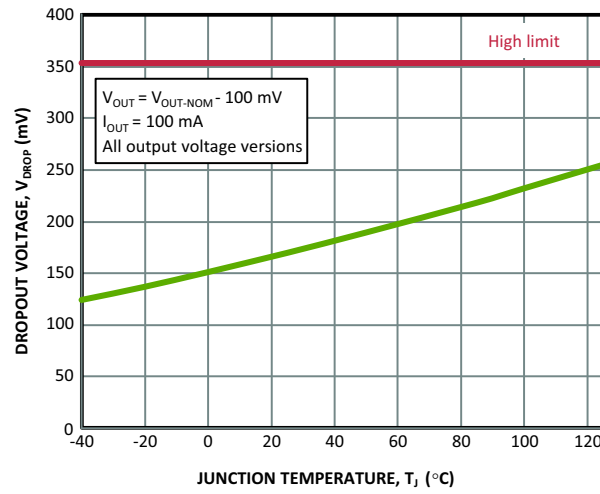


Figure 12. Dropout Voltage vs. Temperature

TYPICAL CHARACTERISTICS

$V_{IN} = V_{OUT-NOM} + 1\text{ V}$ AND $V_{IN} \geq 2.7\text{ V}$, $V_{EN} = 1.2\text{ V}$, $I_{OUT} = 1\text{ mA}$, $C_{OUT} = 1.0\text{ MF}$, ADJ TIED TO OUT, $T_J = 25^\circ\text{C}$, UNLESS OTHERWISE SPECIFIED

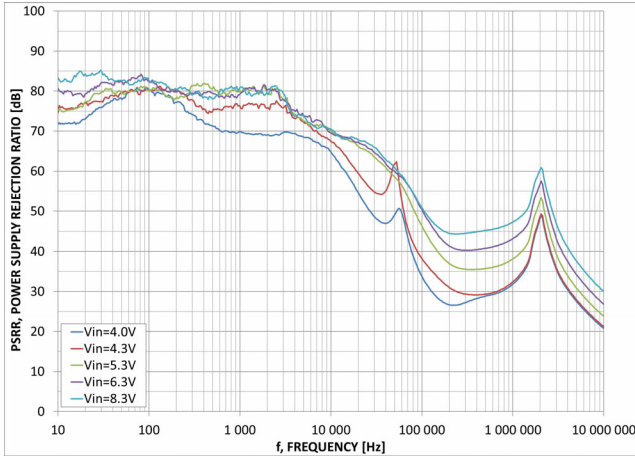


Figure 13. PSRR – FIX–3.3 V, $C_{OUT} = 1\text{ }\mu\text{F}$, $I_{OUT} = 100\text{ mA}$

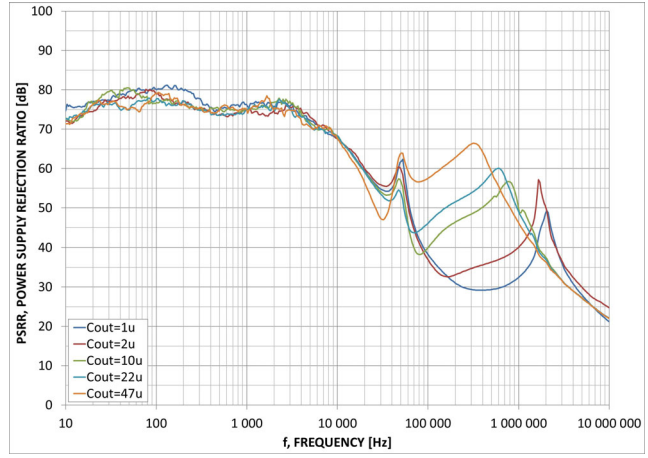


Figure 14. PSRR – FIX–3.3 V, $V_{IN} = 4.3\text{ V}$, $I_{OUT} = 100\text{ mA}$

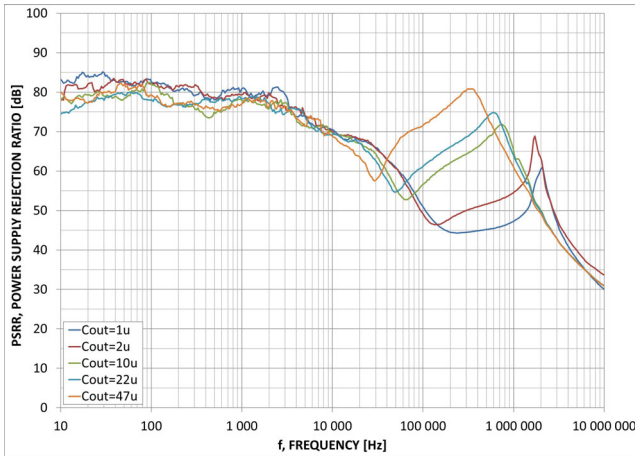


Figure 15. PSRR – FIX–3.3 V, $V_{IN} = 8.3\text{ V}$, $I_{OUT} = 100\text{ mA}$

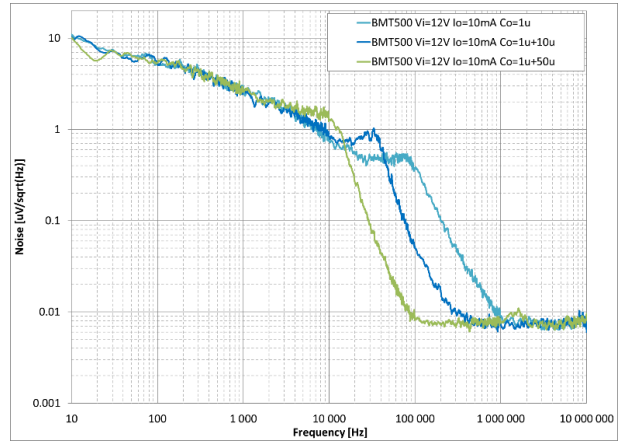


Figure 16. Noise – FIX – 5.0 V, $I_{OUT} = 10\text{ mA}$, Different C_{OUT}

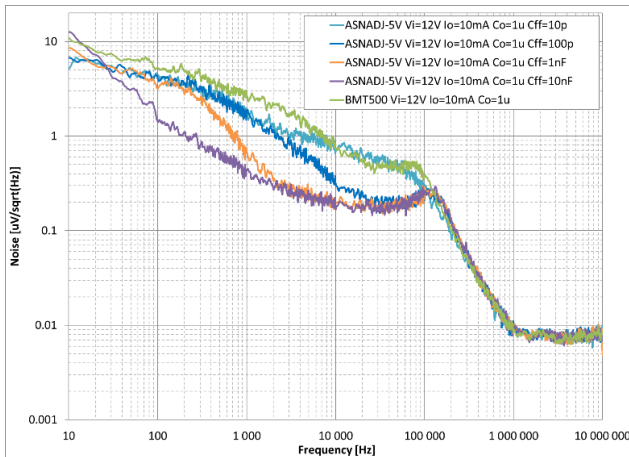


Figure 17. Noise – ADJ–set–5.0 V with Different C_{FF} and FIX – 5.0 V

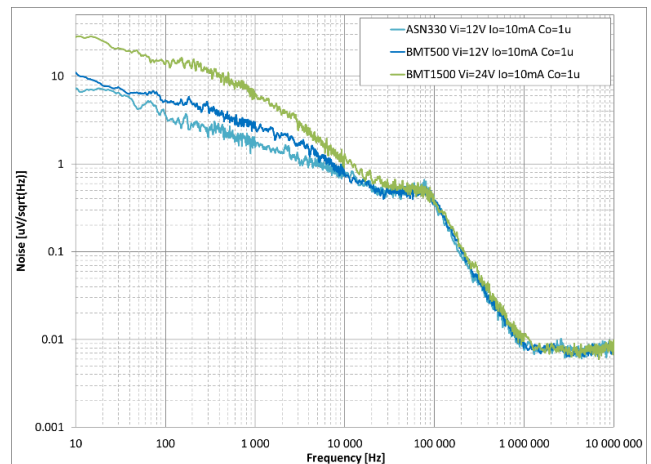


Figure 18. Noise – FIX, $I_{OUT} = 10\text{ mA}$, $C_{OUT} = 1\text{ }\mu\text{F}$, Different V_{OUT}

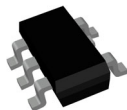
NCV8711

ORDERING INFORMATION

Part Number	Marking	Voltage Option (V _{OUT-NOM})	Version	Package	Shipping
NCV8711ASNADJT1G	GGA	ADJ	Without PG	TSOP-5 (Pb-Free)	3000 / Tape & Reel
NCV8711ASN300T1G	GGC	3.0 V			
NCV8711ASN330T1G	GGD	3.3 V			
NCV8711ASN500T1G	GGE	5.0 V			
NCV8711BMTWADJTBG	GA	ADJ	With PG	WDFNW6 (Pb-Free)	3000 / Tape & Reel
NCV8711BMTW300TBG	GC	3.0 V			
NCV8711BMTW330TBG	GD	3.3 V			
NCV8711BMTW500TBG	GE	5.0 V			

NOTE: To order other package, voltage version or PG / non PG variant, please contact your ON Semiconductor sales representative.

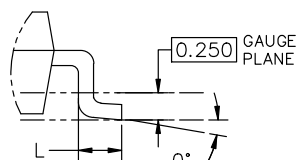
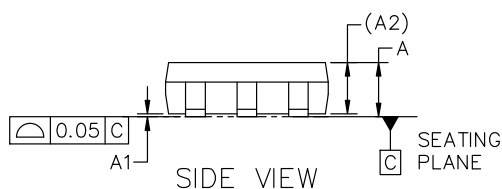
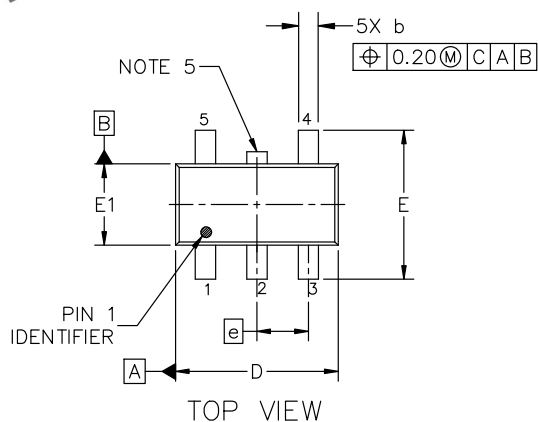



TSOP-5 3.00x1.50x0.95, 0.95P

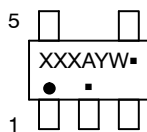
CASE 483

ISSUE P

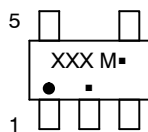
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DETAIL "A"
SCALE 2:1

**GENERIC
MARKING DIAGRAM***


Analog



Discrete/Logic

XXX = Specific Device Code

A = Assembly Location

Y = Year

W = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

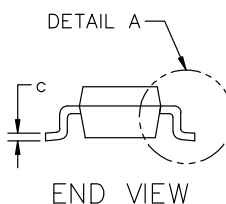
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M = Date Code

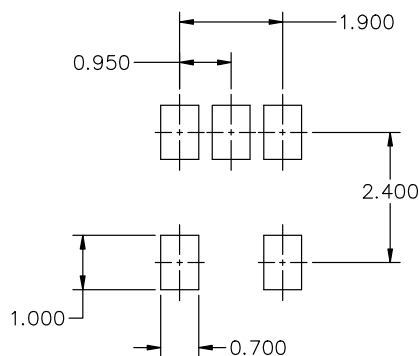
▪ = Pb-Free Package

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES).
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2	0.950 REF.		
b	0.250	0.375	0.500
c	0.100	0.180	0.260
D	2.850	3.000	3.150
E	2.500	2.750	3.000
E1	1.350	1.500	1.650
e	0.950 BSC		
L	0.200	0.400	0.600
θ	0°	5°	10°


RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

DOCUMENT NUMBER: 98ARB18753C

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DESCRIPTION: TSOP-5 3.00x1.50x0.95, 0.95P

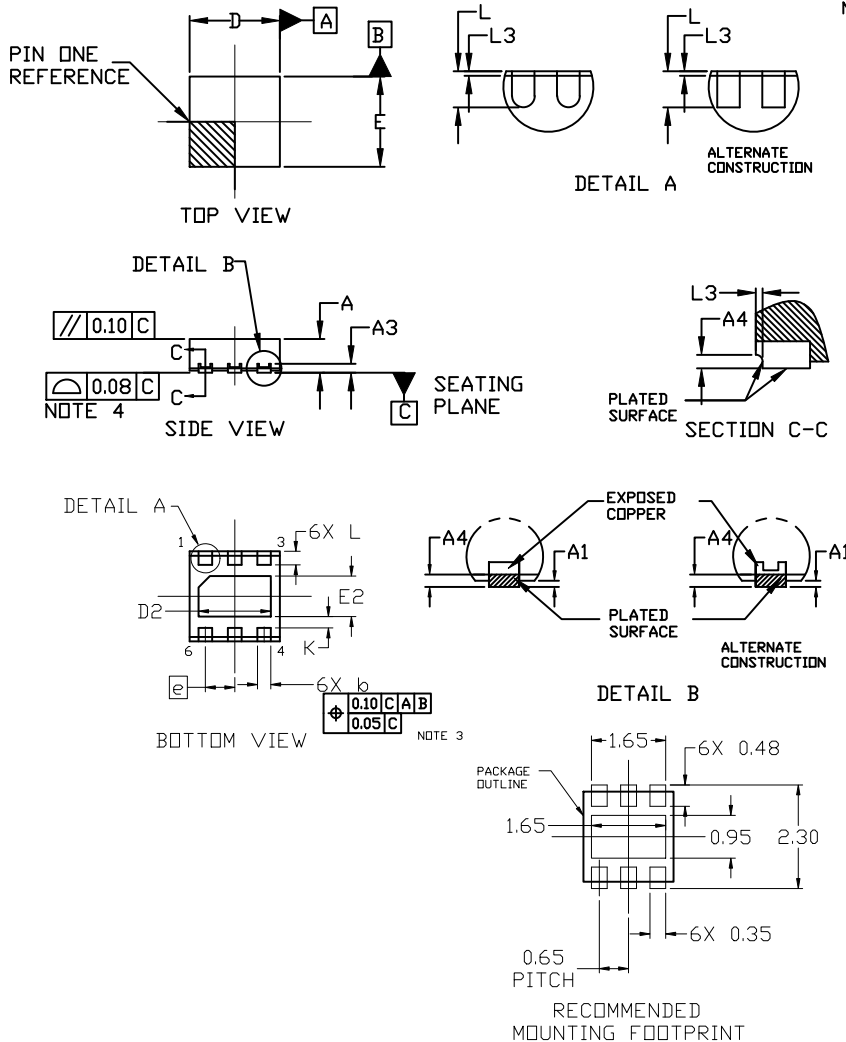
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WDFNW6 2x2, 0.65P
CASE 511DW
ISSUE B

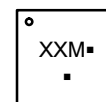
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SCALE 4:1


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION **b** APPLIES TO PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. THIS DEVICE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	---	---	0.05
A3	0.20 REF		
A4	0.10	---	---
b	0.25	0.30	0.35
D	1.90	2.00	2.10
D2	1.50	1.60	1.70
E	1.90	2.00	2.10
E2	0.80	0.90	1.00
e	0.65 BSC		
K	0.25 REF		
L	0.25	0.30	0.35
L3	0.05 REF		

GENERIC MARKING DIAGRAM*


M = Month Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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